

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	169	(ale ald (atomic adj layer)) and (tantalum ta hafnium hf zirconium zr "zro.sub.2" "hfo.sub.2" "ta.sub.2 o.sub.5" "ta.sub.2o.sub.5")	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/26 08:00
L2	395	(((ale ald alcvd (atomic adj layer)) same (tantalum ta "ta.sub.2 o.sub.5" "ta.sub.2o.sub.5")) and capacitor	US-PGPUB; USPAT	OR	ON	2005/01/26 08:46
L3	5209	438/240.ccls. 438/253.ccls. 438/255.ccls. 438/396.ccls. 438/398.ccls. 438/591.ccls. 438/785.ccls.	US-PGPUB; USPAT	OR	OFF	2005/01/26 10:40
L5	766	((chemical adj vapor) \$3cvd) same (oxid\$7 near4 gas) same (metal tantalum ta hafnium hf zirconium zr)	US-PGPUB; USPAT	OR	ON	2005/01/26 10:52
L7	7184	((chemical adj vapor) \$3cvd) and ((oxid\$7 with (gas flow sccm)) same (metal tantalum ta hafnium hf zirconium zr))	US-PGPUB; USPAT	OR	ON	2005/01/26 10:54
L8	516	3 and 7	US-PGPUB; USPAT	OR	ON	2005/01/26 10:49
L9	3095	((chemical adj vapor) \$3cvd) and ((oxid\$7 near4 (gas flow sccm)) same (metal tantalum ta hafnium hf zirconium zr))	US-PGPUB; USPAT	OR	ON	2005/01/26 10:50
L10	264	3 and 9	US-PGPUB; USPAT	OR	ON	2005/01/26 10:56
L11	759	5 and (silicon semiconductor wafer substrate)	US-PGPUB; USPAT	OR	ON	2005/01/26 10:52
L13	652	((chemical adj vapor) \$3cvd) and ((oxid\$7 with (gas flow sccm)) same (metal tantalum ta hafnium hf zirconium zr))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/26 10:55
L14	199	((chemical adj vapor) \$3cvd) and ((oxid\$7 near4 (gas flow sccm)) with (metal tantalum ta hafnium hf zirconium zr))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/26 14:40
L15	192	((chemical adj vapor) \$3cvd) same ((oxid\$7 near2 (gas flow sccm)) with (metal tantalum ta hafnium hf zirconium zr))	US-PGPUB; USPAT	OR	ON	2005/01/26 12:47